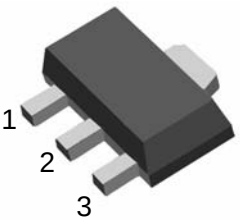
Transys Electronics LIMITED

SOT-89 Plastic-Encapsulated Transistors

2SB1188 TRANSISTOR (PNP)

SOT-89

1. BASE
2. COLLECTO 1
3. EMITTER 3



FEATURES

Power dissipation

P_{CM}: 0.5 W (Tamb=25℃)

Collector current

I_{CM}: -2 A

Collector-base voltage

$V_{(BR)CBO}$: -40 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic=-50μA , I_E=0	-40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C= -1mA , I_B=0	-32		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-50μA, I_C=0	-5		V
Collector cut-off current	I_{CBO}	V_{CB}=-20 V , I_E=0		-1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-4 V , I_C=0		-1	μA
DC current gain *	h_{FE}	V_{CE}=-3V, I_C= -0.5A	82	390	
Collector-emitter saturation voltage *	$V_{Ce(sat)}$	I_C=-2A, I_B= -0.2A		-0.8	V
Transition frequency	f_T	V_{CE}=-5V, I_C=-0.5A ,f=30MHz	80		MHz
Output capacitance	C_{ob}	V_{CB}=-10V, I_E=0 ,f=1MHz		65	pF

* **Measured using pulse current.**

CLASSIFICATION OF h_{FE}

Rank	p	Q	R
Range	82-180	120-270	180-390
Marking	**BCP**	**BCQ**	**BCR**